

EconoPACK™2 Modul mit schnellem Trench/Feldstop IGBT3 und High Efficiency Diode  
EconoPACK™2 with fast trench/fieldstop IGBT3 and EmCon High Efficiency diode

**IGBT, Wechselrichter / IGBT, Inverter Vorläufige Daten / Preliminary Data**  
**Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$	$I_{C\text{ nom}}$ $I_C$	25 40	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	50	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$	$P_{tot}$	145	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		$V_{GES}$	+/-20	V

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,70 1,90	2,15	V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 1,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{ eth}}$	5,0	5,8	6,5 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,24		$\mu\text{C}$
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{ int}}$	8,0		$\Omega$
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	1,80		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,064		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		5,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ on}}$	0,09 0,09		$\mu\text{s}$ $\mu\text{s}$
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_r$	0,03 0,05		$\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ off}}$	0,42 0,52		$\mu\text{s}$ $\mu\text{s}$
Fallzeit, induktive Last Fall time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_f$	0,07 0,09		$\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 70\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{on}$	2,50		mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 70\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 36\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{off}$	2,90		mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$	$I_{SC}$	100		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		$R_{th\text{ JC}}$		0,86	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{th\text{ CH}}$	0,19		K/W

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**Vorläufige Daten**  
**Preliminary Data**

**Diode, Wechselrichter / Diode, Inverter**  
**Höchstzulässige Werte / Maximum Rated Values**

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
Dauergleichstrom Continuous DC forward current		$I_F$	25	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1 \text{ ms}$	$I_{FRM}$	50	A
Grenzlastintegral $I^2t$ - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	170	$\text{A}^2\text{s}$

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 25 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 25 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_F$	1,65 1,65	2,15	V V
Rückstromspitze Peak reverse recovery current	$I_F = 25 \text{ A}, -di_F/dt = 1100 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$	33,0 35,0		A A
Sperrverzögerungsladung Recovered charge	$I_F = 25 \text{ A}, -di_F/dt = 1100 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$Q_r$	2,60 4,90		$\mu\text{C}$ $\mu\text{C}$
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 25 \text{ A}, -di_F/dt = 1100 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$	1,10 2,10		mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		$R_{thJC}$		1,50	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{paste} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,32		K/W

**NTC-Widerstand / NTC-Thermistor**

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_C = 25^{\circ}\text{C}$		$R_{25}$	5,00		k $\Omega$
Abweichung von R100 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$		$\Delta R/R$	-5	5	%
Verlustleistung Power dissipation	$T_C = 25^{\circ}\text{C}$		$P_{25}$		20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		$B_{25/50}$	3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		$B_{25/80}$	t.b.d.		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		$B_{25/100}$	t.b.d.		K

Angaben gemäß gültiger Application Note.  
Specification according to the valid application note.

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